Description

The DCSD24C-L is designed to replace multilayer varistors(MLVs) in portable applications such as cell phones, notebook computers and PDA's, using monolithic silicon technology to provide fast response time and ultra low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The DCSD24C-L complies with the IEC 61000-4-2 (ESD) standard with ±25kV air and ±20kV contact discharge. It is assembled into a lead-free SOD-323 package and will protect one bidirectional line. These devices will fit on the same PCB pad area as an 0805 MLV device.

Features

- 90W peak pulse power (8/20μs)
- Protects one data or power line
- Ultra low leakage：nA level
- Operating voltage：24V
- Ultra low clamping voltage
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    Air discharge: ±25kV
    Contact discharge: ±20kV
  - IEC61000-4-4 (EFT) 40A (5/50ns)
  - IEC61000-4-5 (Lightning) 2A (8/20μs)
- RoHS Compliant

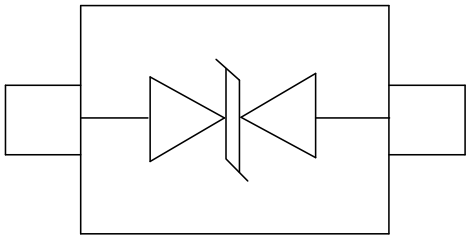
Mechanical Characteristics

- Package: SOD-323
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Peripherals
- Pagers Peripherals
- Desktop and Servers

Dimensions and Pin Configuration



Circuit and Pin Schematic

Marking Information

24L = Device Marking Code

Ordering Information

Part Number	Marking	Packaging	Reel Size
DCSD24C-L	24L	3000/Tape & Reel	7 inch

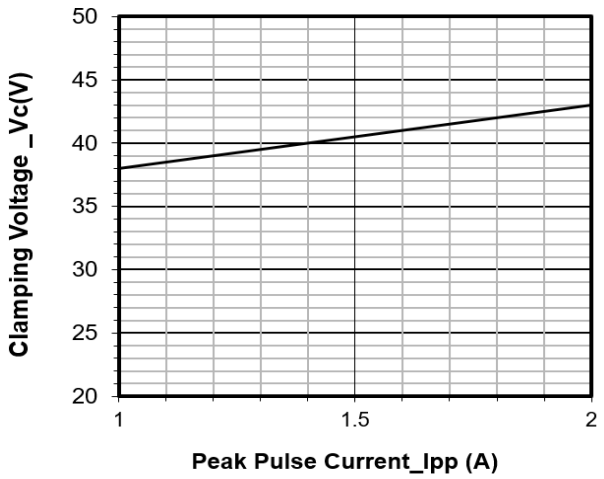
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	90	W
Peak Pulse Current (8/20μs)	Ipp	2	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±25 ±20	kV
Operating Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

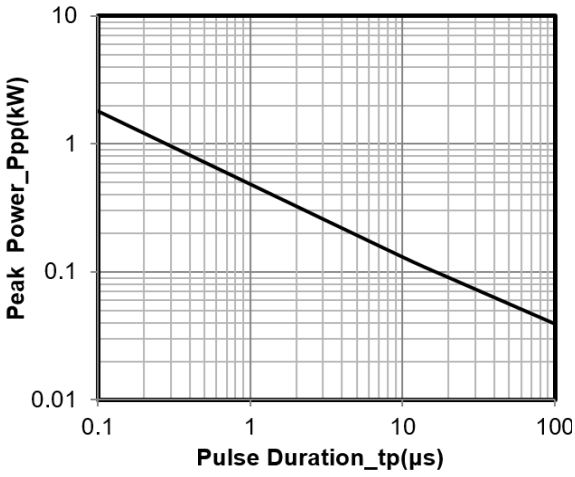
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			24	V	
Breakdown Voltage	V_{BR}	27			V	I_T = 1mA
Reverse Leakage Current	I_R			0.2	μA	V_{RWM} = 24V
Clamping Voltage	V_C			38	V	I_{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V_C			45	V	I_{PP} = 2A (8 x 20μs pulse)
Junction Capacitance	C_J		8		pF	VR = 0V, f = 1MHz

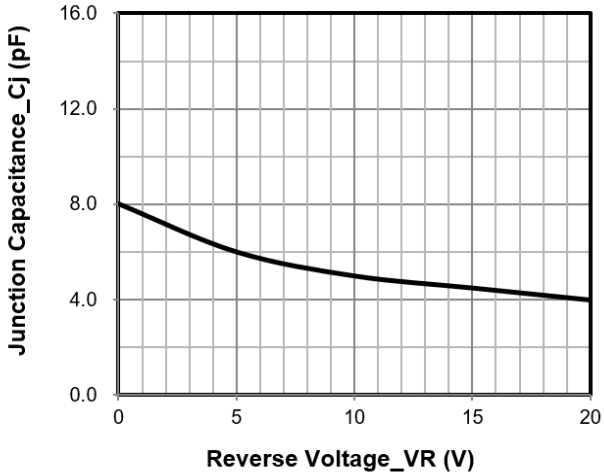
Typical Performance Characteristics (T_A=25℃ unless otherwise Specified)



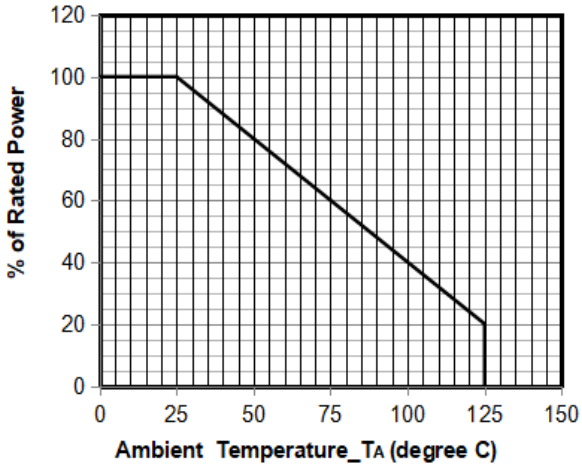
Junction Capacitance vs. Reverse Voltage



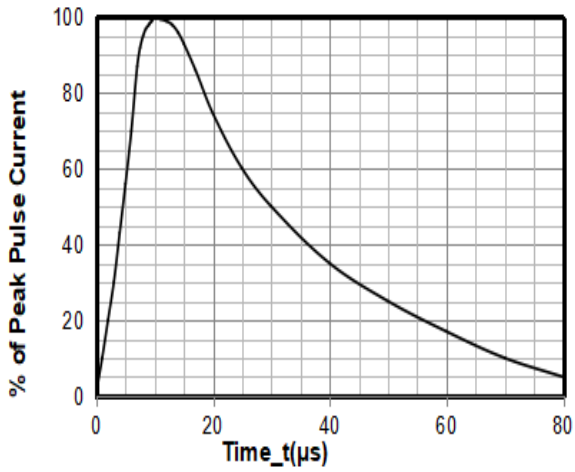
Peak Pulse Power vs. Pulse Time



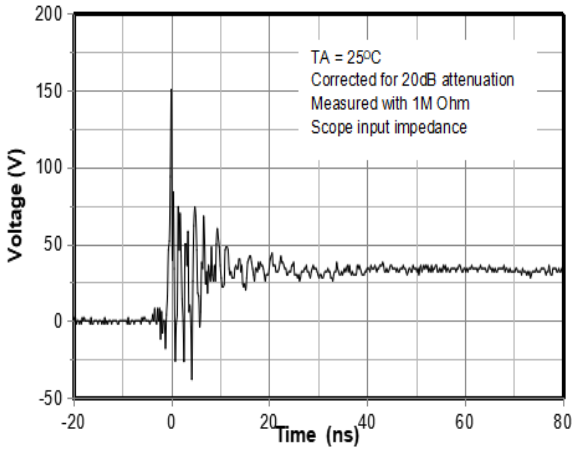
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



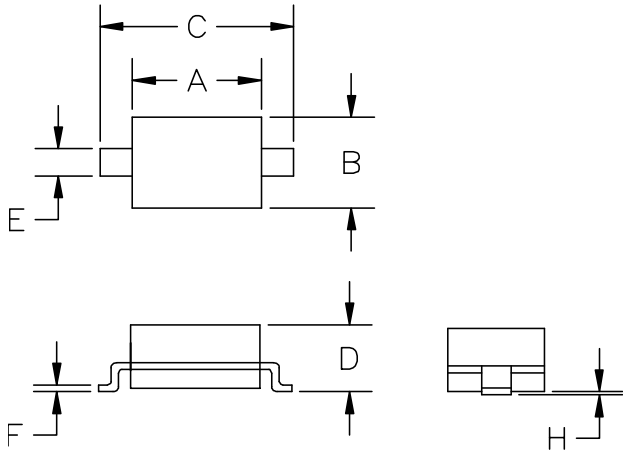
8 X 20μs Pulse Waveform



ESD Clamping Voltage

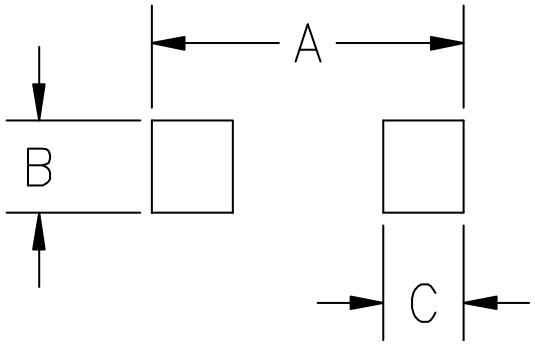
8 kV Contact per IEC61000−4−2

SOD-323 Package Outline Drawing



SYM	DIMENSIO			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.50	1.80	0.060	0.071
B	1.20	1.40	0.045	0.054
C	2.30	2.70	0.090	0.107
D	-	1.10	-	0.043
E	0.30	0.40	0.012	0.016
F	0.10	0.25	0.004	0.010
H	-	0.10	-	0.004

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
A	3.15	0.120
B	0.80	0.031
C	0.80	0.031

Contact Information

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